

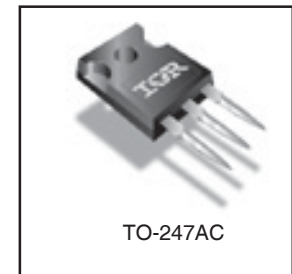
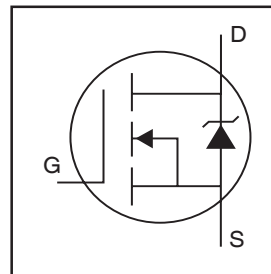
PDP MOSFET

IRFP4232PbF

Features

- Advanced process technology
- Key parameters optimized for PDP Sustain & Energy Recovery applications
- Low E_{PULSE} rating to reduce the power dissipation in Sustain & ER applications
- Low Q_G for fast response
- High repetitive peak current capability for reliable operation
- Short fall & rise times for fast switching
- 175°C operating junction temperature for improved ruggedness
- Repetitive avalanche capability for robustness and reliability

| Key Parameters | | |
|--|-----|----|
| V_{DS} min | 250 | V |
| V_{DS} (Avalanche) typ. | 300 | V |
| $R_{DS(ON)}$ typ. @ 10V | 30 | mΩ |
| E_{PULSE} typ. | 310 | μJ |
| I_{RP} max @ $T_C = 100^\circ\text{C}$ | 117 | A |
| T_J max | 175 | °C |



Description

This HEXFET[®] Power MOSFET is specifically designed for Sustain; Energy Recovery & Pass switch applications in Plasma Display Panels. This MOSFET utilizes the latest processing techniques to achieve low on-resistance per silicon area and low E_{PULSE} rating. Additional features of this MOSFET are 175°C operating junction temperature and high repetitive peak current capability. These features combine to make this MOSFET a highly efficient, robust and reliable device for PDP driving applications.

Absolute Maximum Ratings

| | Parameter | Max. | Units |
|--------------------------------------|--|------------------|-------|
| V_{GS} | Gate-to-Source Voltage | ±20 | V |
| V_{GS} (TRANSIENT) | Gate-to-Source Voltage | ±30 | |
| I_D @ $T_C = 25^\circ\text{C}$ | Continuous Drain Current, V_{GS} @ 10V | 60 | A |
| I_D @ $T_C = 100^\circ\text{C}$ | Continuous Drain Current, V_{GS} @ 10V | 42 | |
| I_{DM} | Pulsed Drain Current ① | 240 | |
| I_{RP} @ $T_C = 100^\circ\text{C}$ | Repetitive Peak Current ⑤ | 117 | |
| P_D @ $T_C = 25^\circ\text{C}$ | Power Dissipation | 430 | W |
| P_D @ $T_C = 100^\circ\text{C}$ | Power Dissipation | 210 | |
| | Linear Derating Factor | 2.9 | W/°C |
| T_J | Operating Junction and Storage Temperature Range | -40 to + 175 | °C |
| T_{STG} | | | |
| | Soldering Temperature for 10 seconds | 300 | |
| | Mounting Torque, 6-32 or M3 Screw | 10lb·in (1.1N·m) | N |

Thermal Resistance

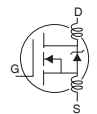
| | Parameter | Typ. | Max. | Units |
|-----------------|--------------------|------|------|-------|
| $R_{\theta JC}$ | Junction-to-Case ④ | — | 0.35 | °C/W |

Notes ① through ⑤ are on page 8

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|--------------------------------|--------------------------------------|------|------|------|-------|---|
| BV_{DSS} | Drain-to-Source Breakdown Voltage | 250 | — | — | V | $V_{GS} = 0V, I_D = 250\mu A$ |
| $\Delta BV_{DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient | — | 180 | — | mV/°C | Reference to $25^\circ\text{C}, I_D = 1mA$ |
| $R_{DS(on)}$ | Static Drain-to-Source On-Resistance | — | 30 | 35.7 | mΩ | $V_{GS} = 10V, I_D = 42A$ ③ |
| $V_{GS(th)}$ | Gate Threshold Voltage | 3.0 | — | 5.0 | V | $V_{DS} = V_{GS}, I_D = 250\mu A$ |
| $\Delta V_{GS(th)}/\Delta T_J$ | Gate Threshold Voltage Coefficient | — | -15 | — | mV/°C | |
| I_{DSS} | Drain-to-Source Leakage Current | — | — | 5.0 | μA | $V_{DS} = 200V, V_{GS} = 0V$ |
| | | — | — | 150 | | $V_{DS} = 200V, V_{GS} = 0V, T_J = 125^\circ\text{C}$ |
| I_{GSS} | Gate-to-Source Forward Leakage | — | — | 100 | nA | $V_{GS} = 20V$ |
| | Gate-to-Source Reverse Leakage | — | — | -100 | | $V_{GS} = -20V$ |
| g_{fs} | Forward Transconductance | 95 | — | — | S | $V_{DS} = 25V, I_D = 42A$ |
| Q_g | Total Gate Charge | — | 160 | 240 | nC | $V_{DD} = 125V, I_D = 42A, V_{GS} = 10V$ ③ |
| Q_{gd} | Gate-to-Drain Charge | — | 60 | — | | |
| $t_{d(on)}$ | Turn-On Delay Time | — | 37 | — | ns | $V_{DD} = 125V, V_{GS} = 10V$ ③ $I_D = 42A$ $R_G = 5.0\Omega$ See Fig. 22 |
| t_r | Rise Time | — | 100 | — | | |
| $t_{d(off)}$ | Turn-Off Delay Time | — | 64 | — | | |
| t_f | Fall Time | — | 63 | — | | |
| t_{st} | Shoot Through Blocking Time | 100 | — | — | ns | $V_{DD} = 200V, V_{GS} = 15V, R_G = 4.7\Omega$ |
| E_{PULSE} | Energy per Pulse | — | 310 | — | μJ | $L = 220nH, C = 0.4\mu F, V_{GS} = 15V$ $V_{DS} = 200V, R_G = 4.7\Omega, T_J = 25^\circ\text{C}$ |
| | | — | 950 | — | | $L = 220nH, C = 0.4\mu F, V_{GS} = 15V$ $V_{DS} = 200V, R_G = 4.7\Omega, T_J = 100^\circ\text{C}$ |
| C_{iss} | Input Capacitance | — | 7290 | — | pF | $V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0MHz,$ See Fig.5 $V_{GS} = 0V, V_{DS} = 0V \text{ to } 200V$ |
| C_{oss} | Output Capacitance | — | 610 | — | | |
| C_{rss} | Reverse Transfer Capacitance | — | 240 | — | | |
| $C_{oss \text{ eff.}}$ | Effective Output Capacitance | — | 420 | — | | |
| L_D | Internal Drain Inductance | — | 5.0 | — | nH | Between lead, 6mm (0.25in.) from package and center of die contact |
| L_S | Internal Source Inductance | — | 13 | — | | |

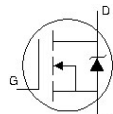


Avalanche Characteristics

| | Parameter | Typ. | Max. | Units |
|---------------------|---------------------------------|------|------|-------|
| E_{AS} | Single Pulse Avalanche Energy ② | — | 220 | mJ |
| E_{AR} | Repetitive Avalanche Energy ① | — | 43 | mJ |
| $V_{DS(Avalanche)}$ | Repetitive Avalanche Voltage ① | 300 | — | V |
| I_{AS} | Avalanche Current ② | — | 42 | A |

Diode Characteristics

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|--------------------------------|--|------|------|------|-------|--|
| $I_S @ T_C = 25^\circ\text{C}$ | Continuous Source Current (Body Diode) | — | — | 60 | A | MOSFET symbol showing the integral reverse p-n junction diode. |
| I_{SM} | Pulsed Source Current (Body Diode) ① | — | — | 240 | | |
| V_{SD} | Diode Forward Voltage | — | — | 1.0 | V | $T_J = 25^\circ\text{C}, I_S = 42A, V_{GS} = 0V$ ③ |
| t_{rr} | Reverse Recovery Time | — | 240 | 360 | ns | $T_J = 25^\circ\text{C}, I_F = 42A, V_{DD} = 50V$ |
| Q_{rr} | Reverse Recovery Charge | — | 1230 | 1850 | nC | $di/dt = 100A/\mu s$ ③ |



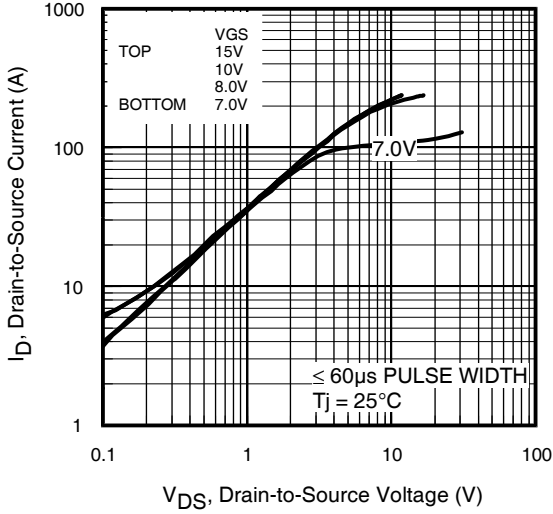


Fig 1. Typical Output Characteristics

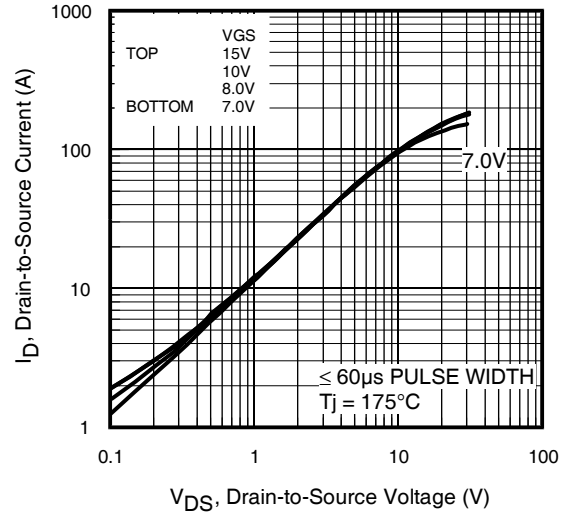


Fig 2. Typical Output Characteristics

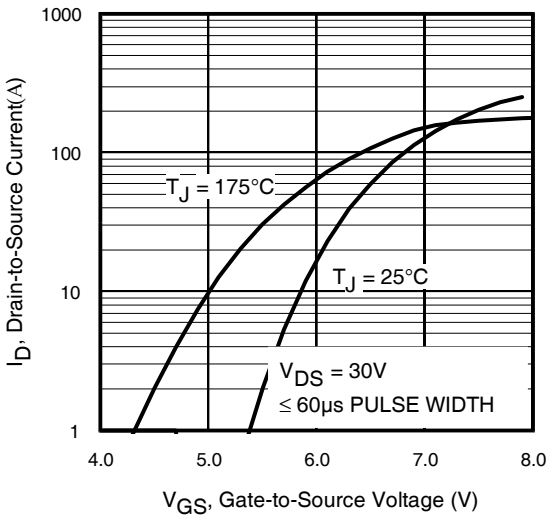


Fig 3. Typical Transfer Characteristics

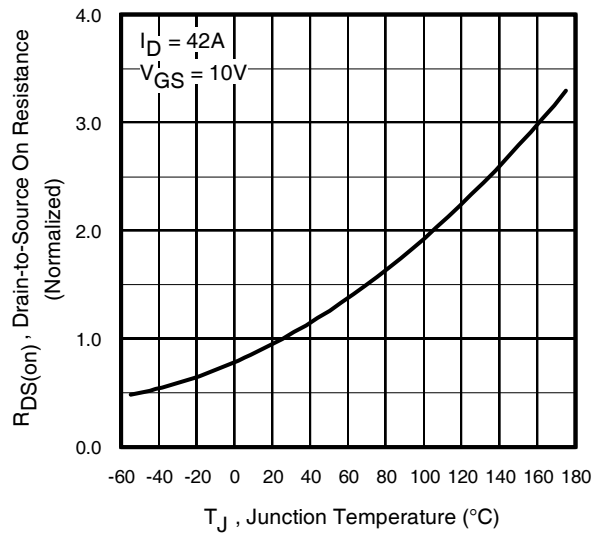


Fig 4. Normalized On-Resistance vs. Temperature

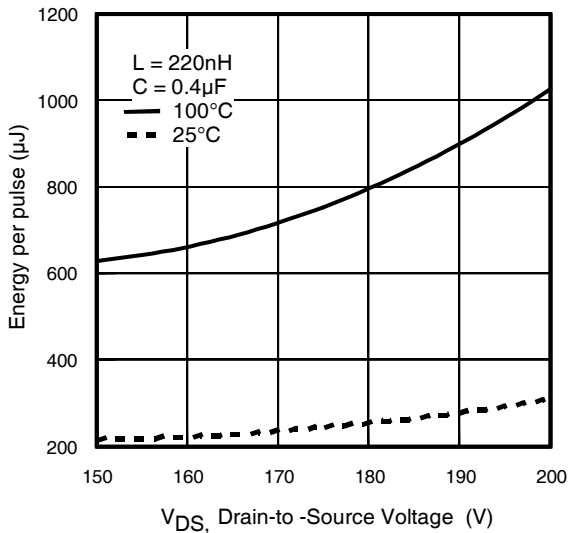


Fig 5. Typical E_{PULSE} vs. Drain-to-Source Voltage

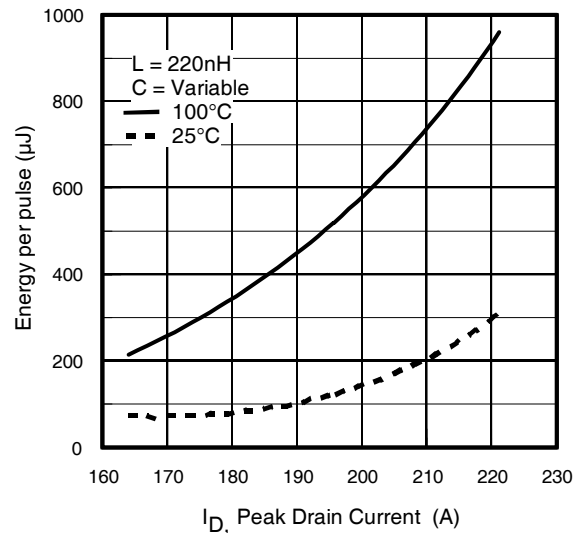


Fig 6. Typical E_{PULSE} vs. Peak Drain Current

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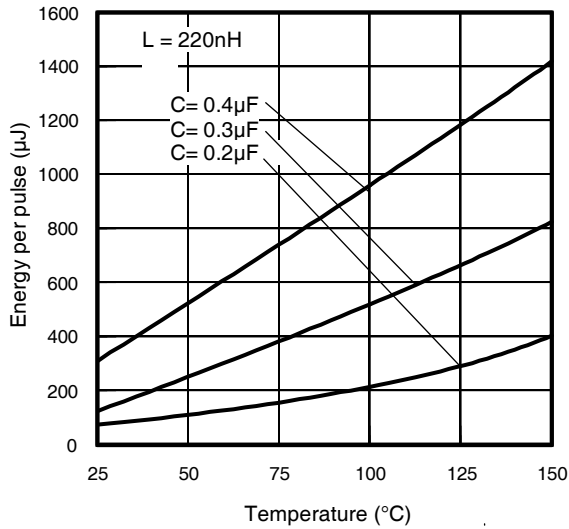


Fig 7. Typical E_{PULSE} vs. Temperature

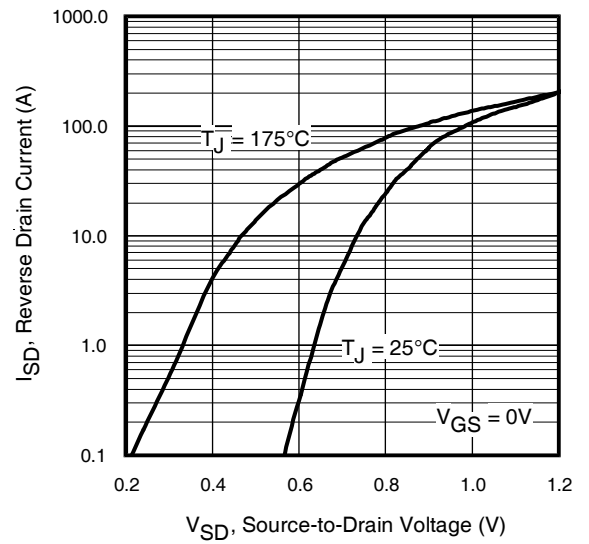


Fig 8. Typical Source-Drain Diode Forward Voltage

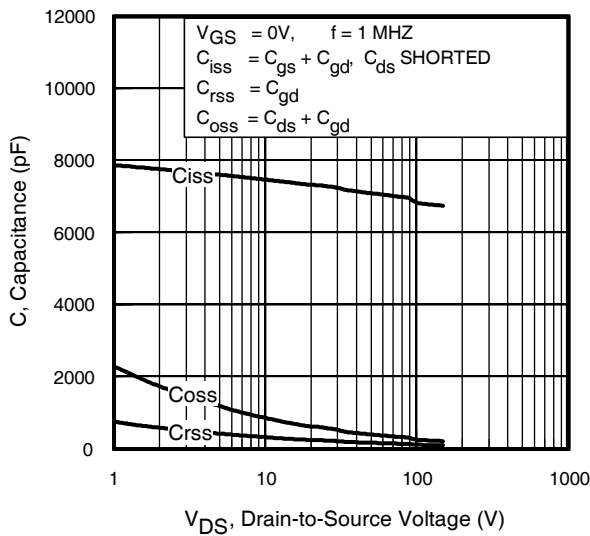


Fig 9. Typical Capacitance vs. Drain-to-Source Voltage

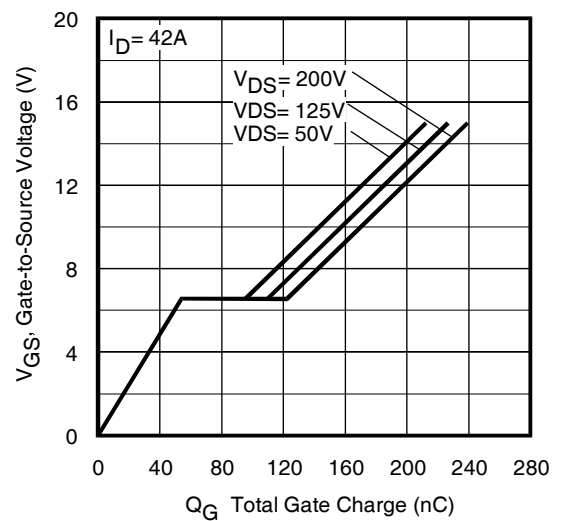


Fig 10. Typical Gate Charge vs. Gate-to-Source Voltage

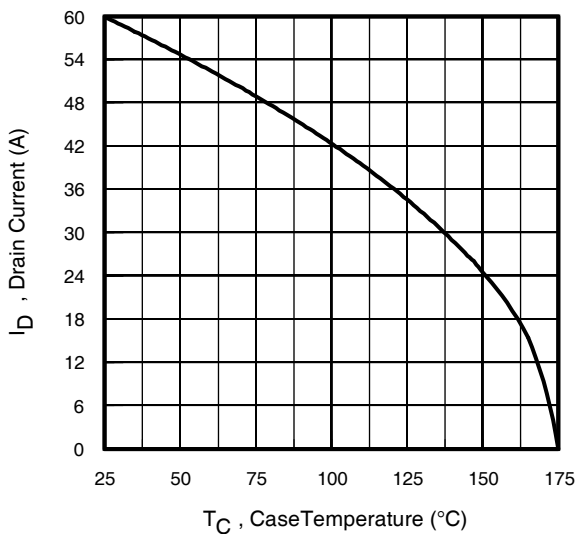


Fig 11. Maximum Drain Current vs. Case Temperature

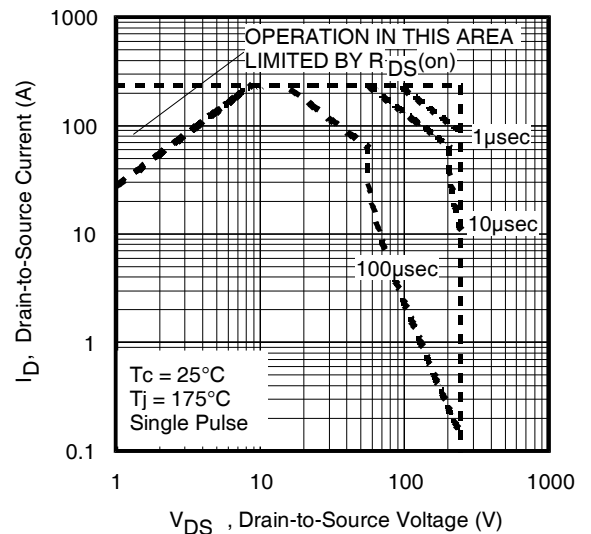


Fig 12. Maximum Safe Operating Area

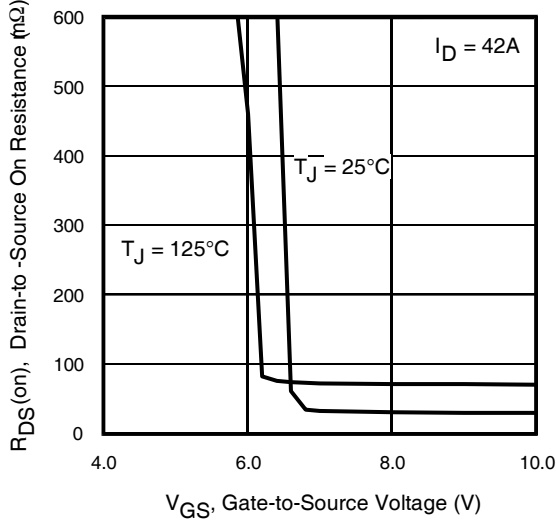


Fig 13. On-Resistance Vs. Gate Voltage

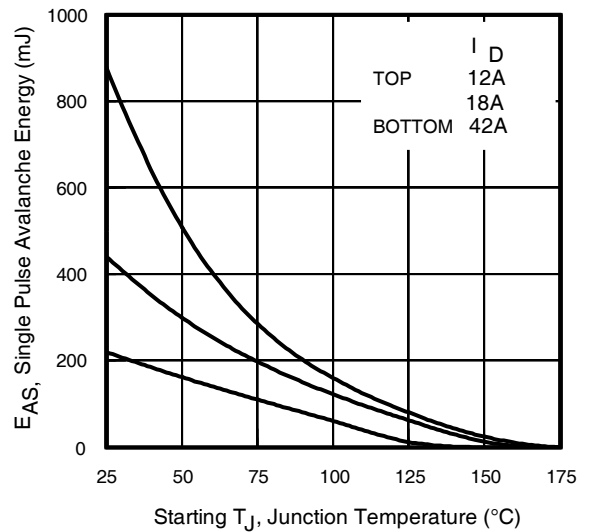


Fig 14. Maximum Avalanche Energy Vs. Temperature

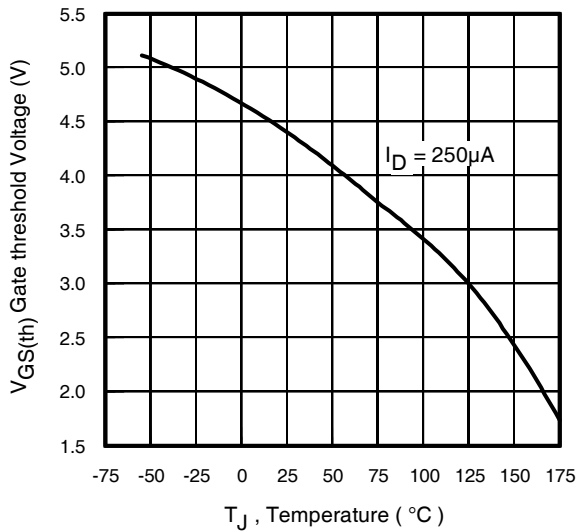


Fig 15. Threshold Voltage vs. Temperature

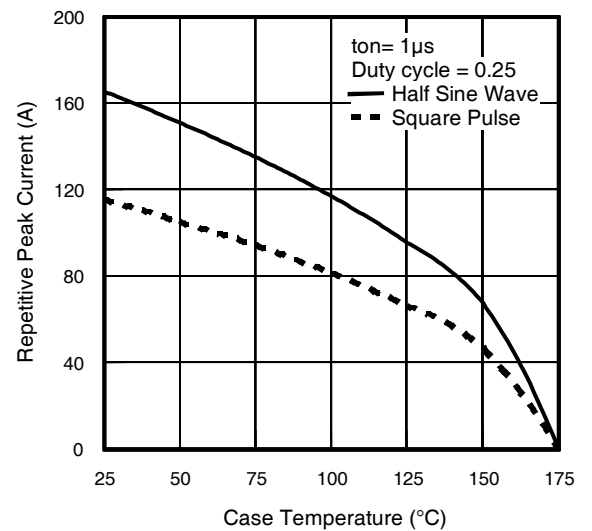


Fig 16. Typical Repetitive peak Current vs. Case temperature

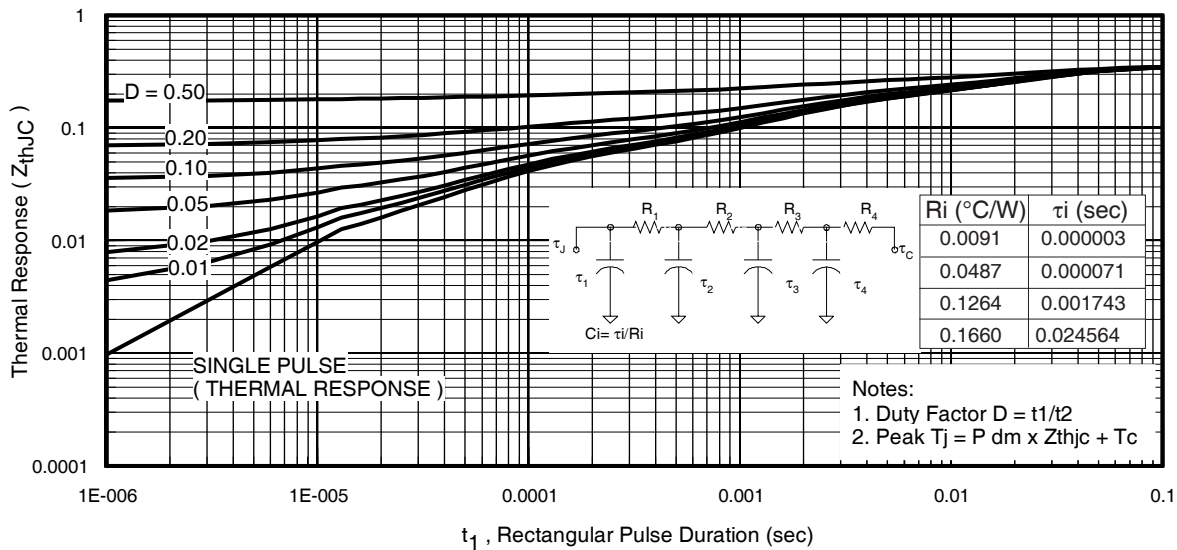
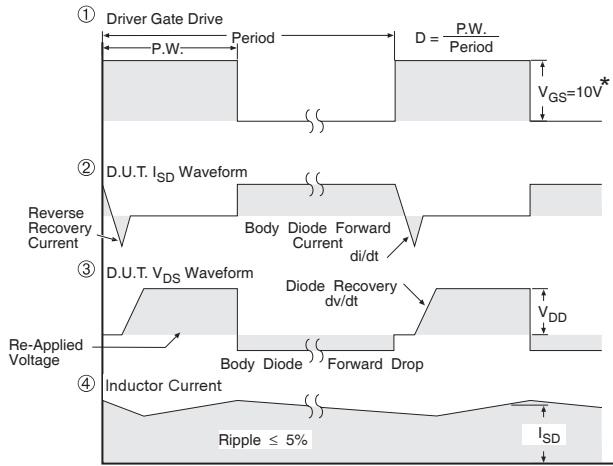
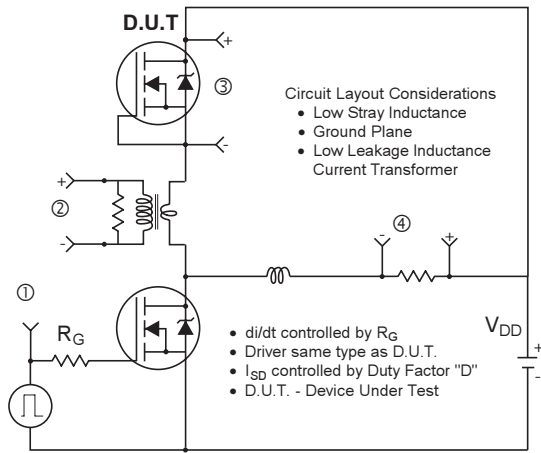


Fig 17. Maximum Effective Transient Thermal Impedance, Junction-to-Case



* $V_{GS} = 5V$ for Logic Level Devices

Fig 18. Diode Reverse Recovery Test Circuit for N-Channel HEXFET® Power MOSFETs

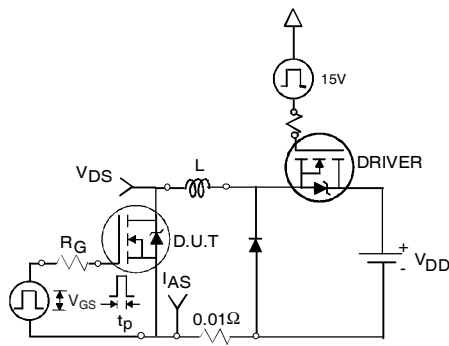


Fig 19a. Unclamped Inductive Test Circuit

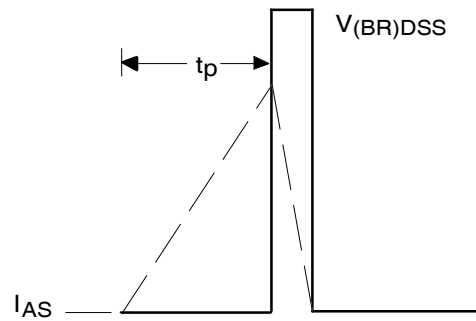


Fig 19b. Unclamped Inductive Waveforms

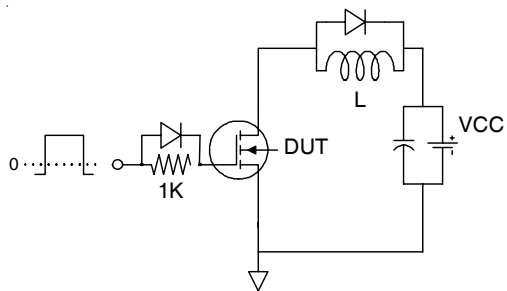


Fig 20a. Gate Charge Test Circuit

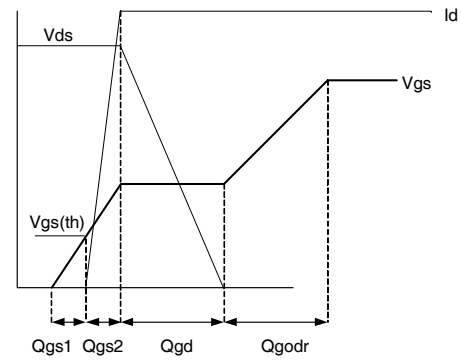


Fig 20b. Gate Charge Waveform

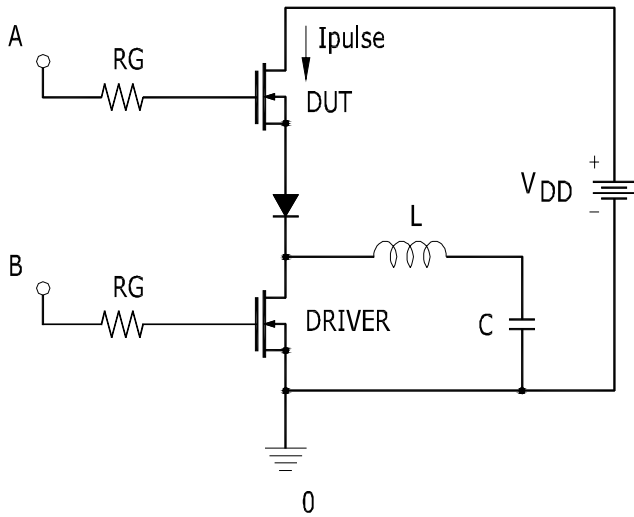


Fig 21a. t_{st} and E_{PULSE} Test Circuit

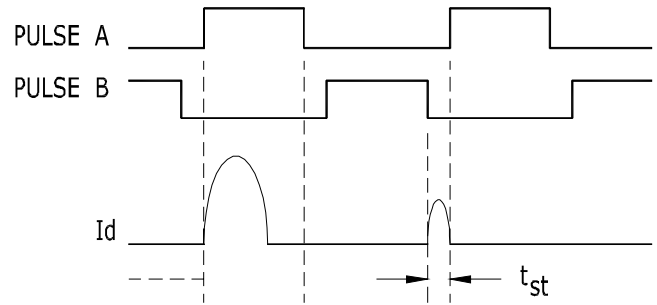


Fig 21b. t_{st} Test Waveforms

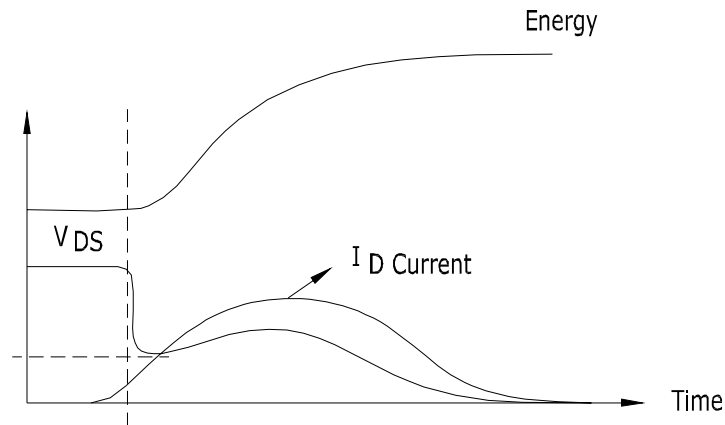


Fig 21c. E_{PULSE} Test Waveforms

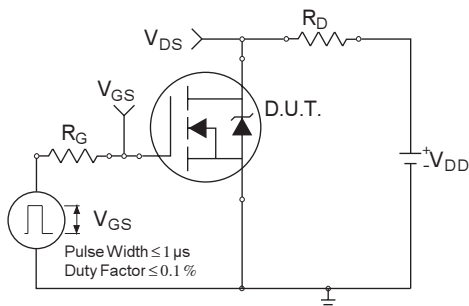


Fig 22a. Switching Time Test Circuit

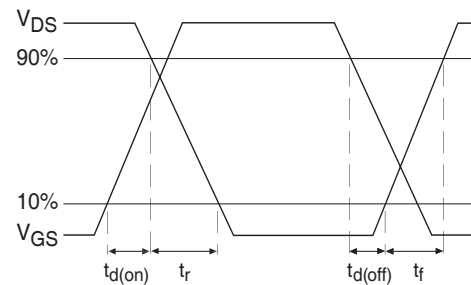
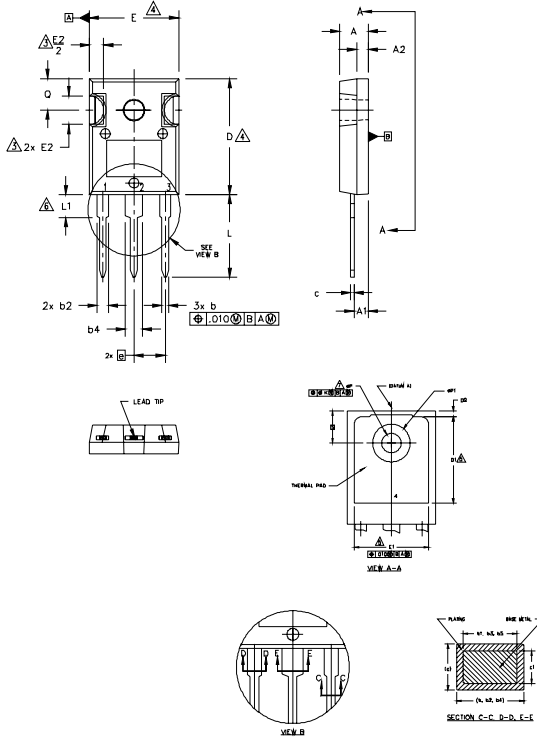


Fig 22b. Switching Time Waveforms

IRFP4232PbF

TO-247AC Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
 2. DIMENSIONS ARE SHOWN IN INCHES.
 3. CONTOUR OF SLOT OPTIONAL.
 4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
 5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
 6. LEAD FINISH UNCONTROLLED IN L1.
 7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
 8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AC .

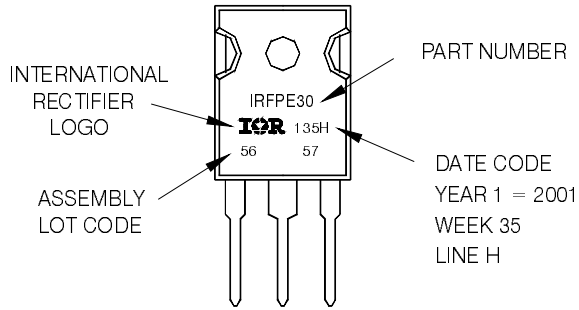
| SYMBOL | DIMENSIONS | | | | NOTES |
|--------|------------|------|-------------|-------|-------|
| | INCHES | | MILLIMETERS | | |
| | MIN. | MAX. | MIN. | MAX. | |
| A | .183 | .209 | 4.65 | 5.31 | |
| A1 | .087 | .102 | 2.21 | 2.59 | |
| A2 | .059 | .098 | 1.50 | 2.49 | |
| b | .039 | .065 | 0.99 | 1.40 | |
| b1 | .039 | .053 | 0.99 | 1.35 | |
| b2 | .065 | .094 | 1.65 | 2.39 | |
| b3 | .065 | .092 | 1.65 | 2.34 | |
| b4 | .102 | .135 | 2.59 | 3.43 | |
| b5 | .102 | .133 | 2.59 | 3.38 | |
| c | .015 | .035 | 0.38 | 0.89 | |
| c1 | .015 | .033 | 0.38 | 0.84 | |
| D | .776 | .815 | 19.71 | 20.70 | 4 |
| D1 | .515 | - | 13.08 | - | 5 |
| D2 | .020 | .053 | 0.51 | 1.35 | |
| E | .602 | .625 | 15.29 | 15.87 | 4 |
| E1 | .530 | - | 13.46 | - | |
| E2 | .178 | .216 | 4.52 | 5.49 | |
| e | .215 BSC | | 5.46 BSC | | |
| Øk | .010 | | 0.25 | | |
| L | .559 | .634 | 14.20 | 16.10 | |
| L1 | .146 | .169 | 3.71 | 4.29 | |
| ØP | .140 | .144 | 3.56 | 3.66 | |
| ØP1 | - | .291 | - | 7.39 | |
| Q | .209 | .224 | 5.31 | 5.69 | |
| S | .217 BSC | | 5.51 BSC | | |

- LEAD ASSIGNMENTS
- HEXFLET
- 1.- GATE
 - 2.- DRAIN
 - 3.- SOURCE
 - 4.- DRAIN
- IGBTs, CoPACK
- 1.- GATE
 - 2.- COLLECTOR
 - 3.- EMITTER
 - 4.- COLLECTOR
- DIODES
- 1.- ANODE/OPEN
 - 2.- CATHODE
 - 3.- ANODE

TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2001
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position
indicates "Lead-Free"



TO-247AC package is not recommended for Surface Mount Application.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 0.25\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 42\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ R_θ is measured at T_J of approximately 90°C .
- ⑤ Half sine wave with duty cycle = 0.25, $t_{on} = 1\mu\text{sec}$.

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

Data and specifications subject to change without notice.
This product has been designed for the Consumer market.
Qualification Standards can be found on IR's Web site.

This datasheet has been downloaded from:

www.DatasheetCatalog.com

Datasheets for electronic components.